

FIG. 1

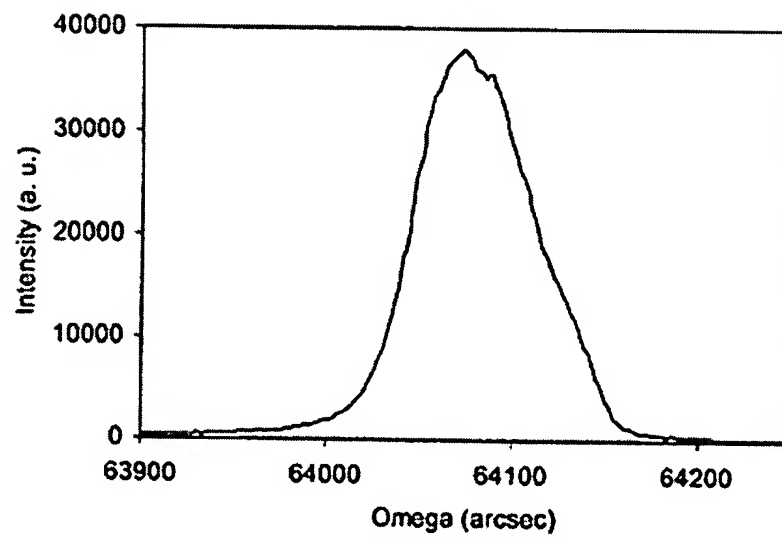


FIG. 2



FIG. 3

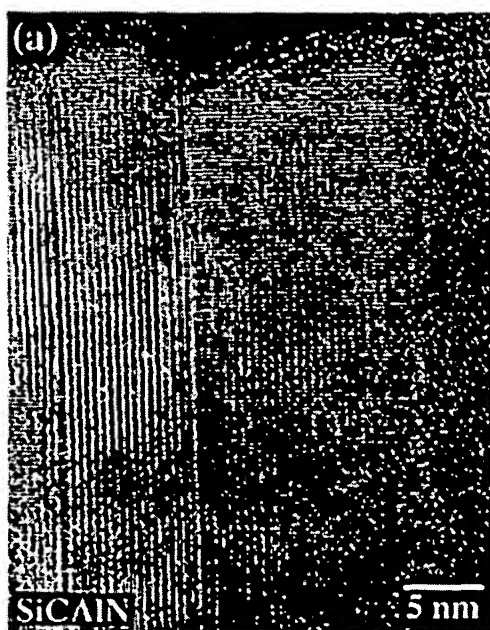


FIG. 4

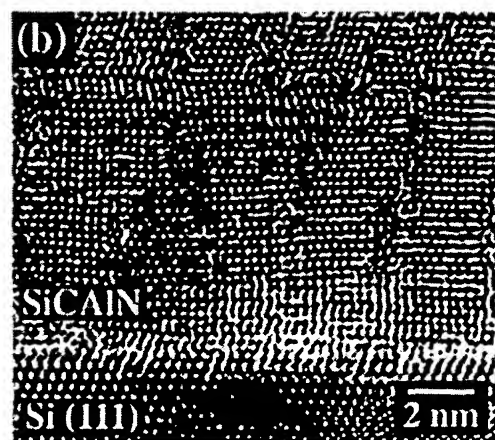


FIG. 5

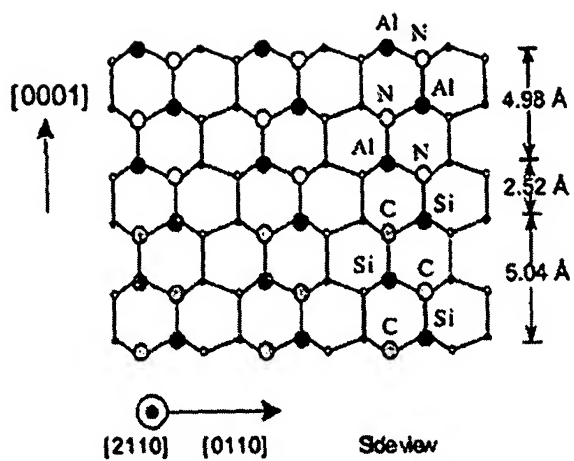


FIG. 6

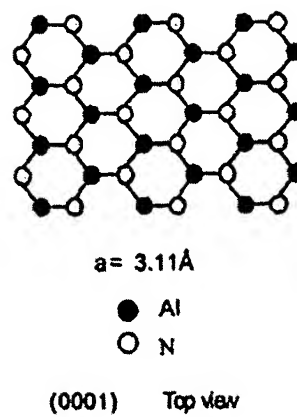


FIG. 7

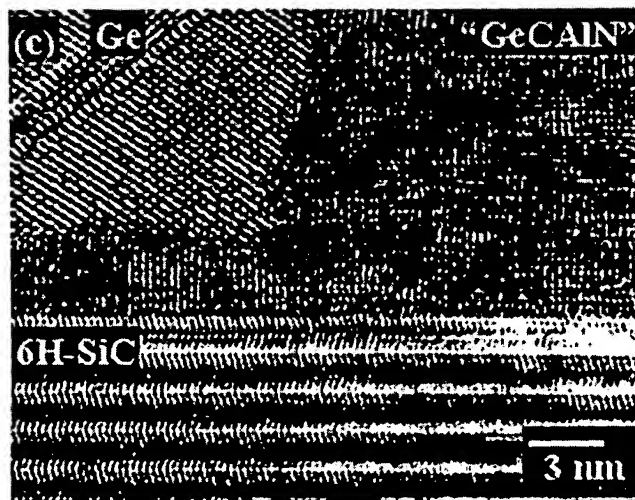


FIG. 8

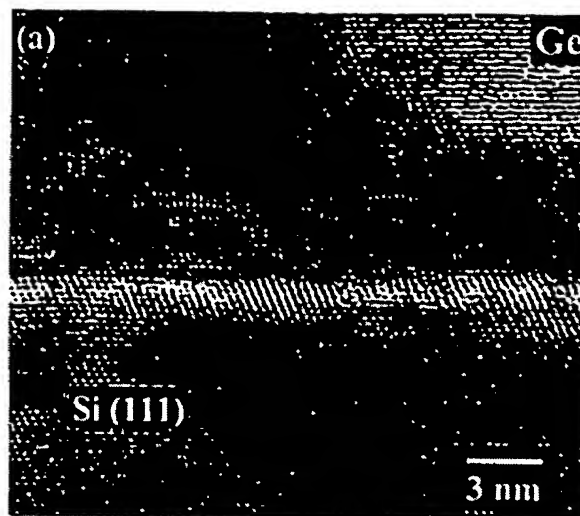


FIG. 9

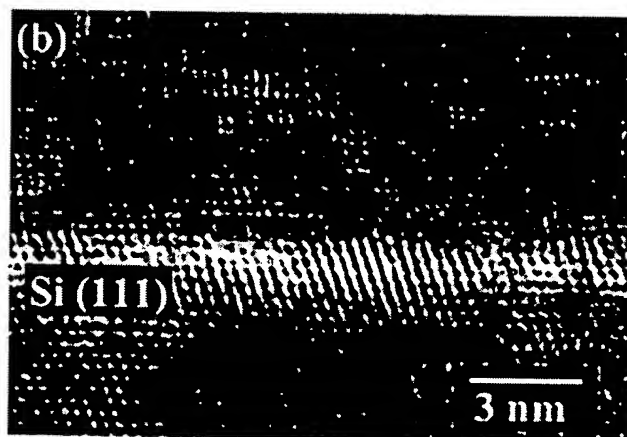


FIG. 10

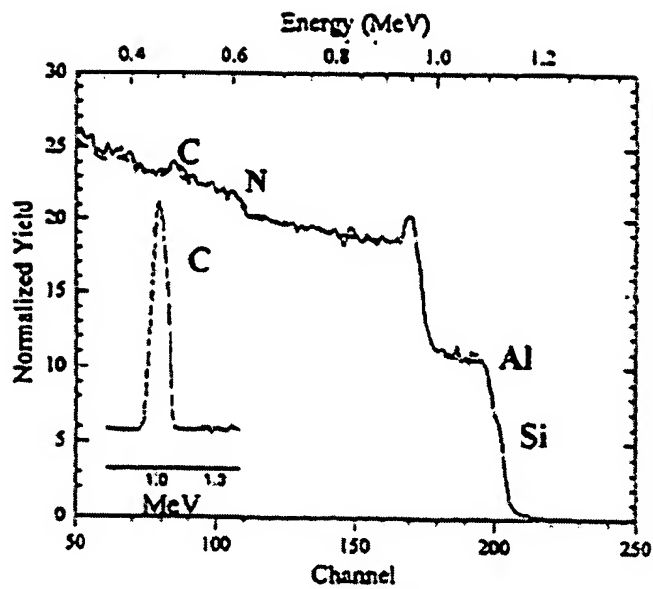


FIG. 11

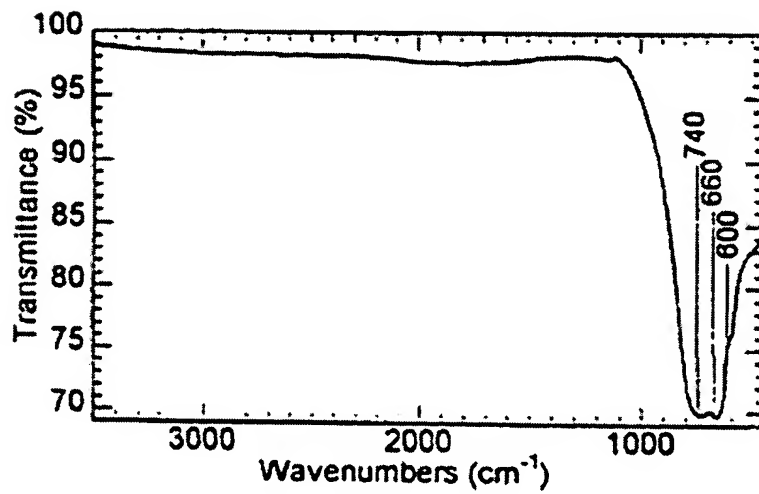


FIG. 12

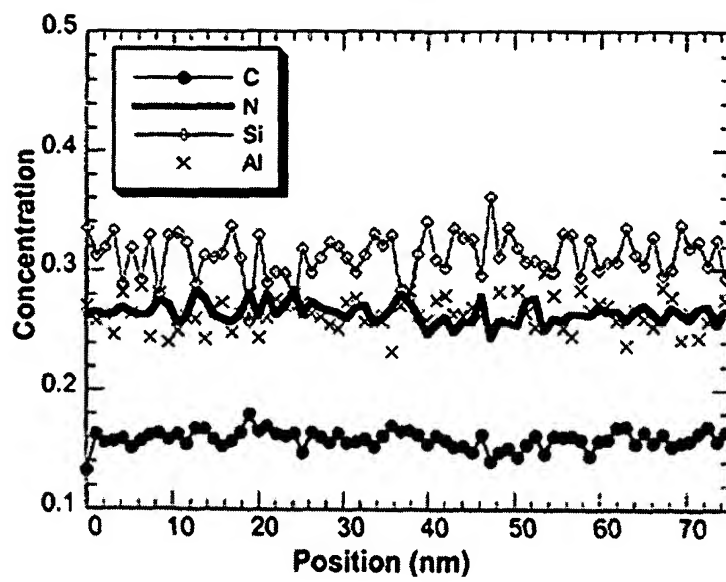


FIG. 13



FIG. 14

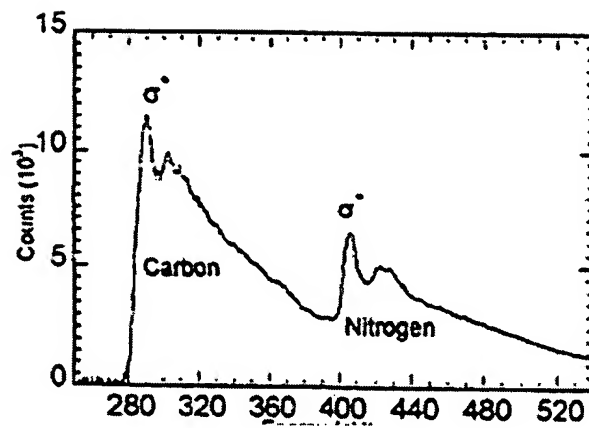
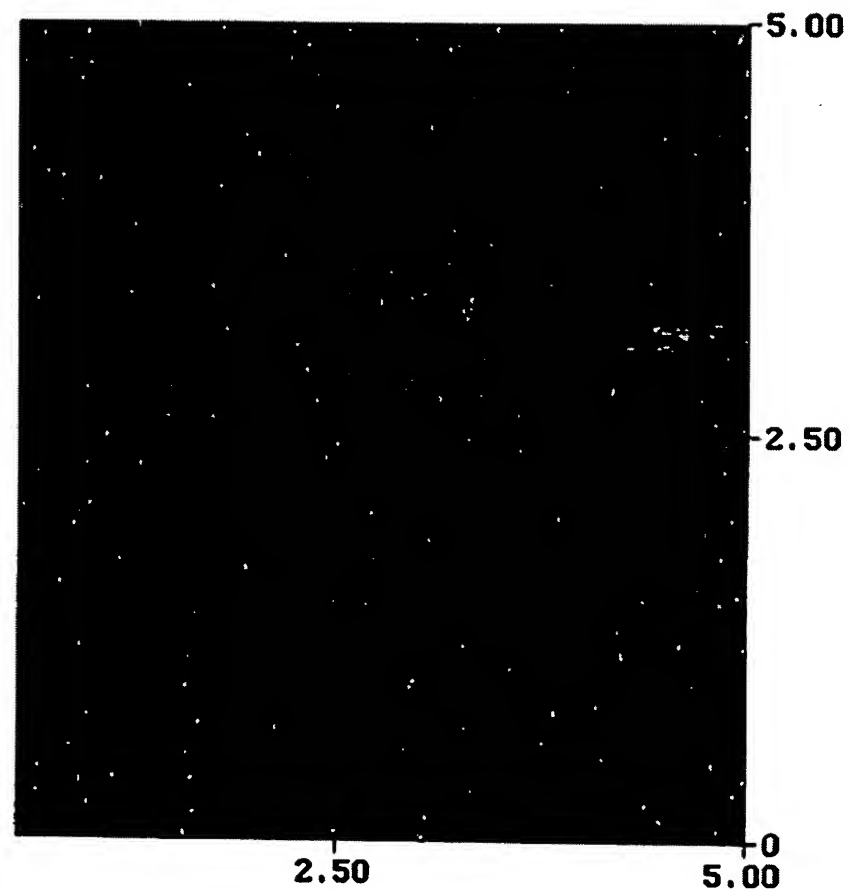
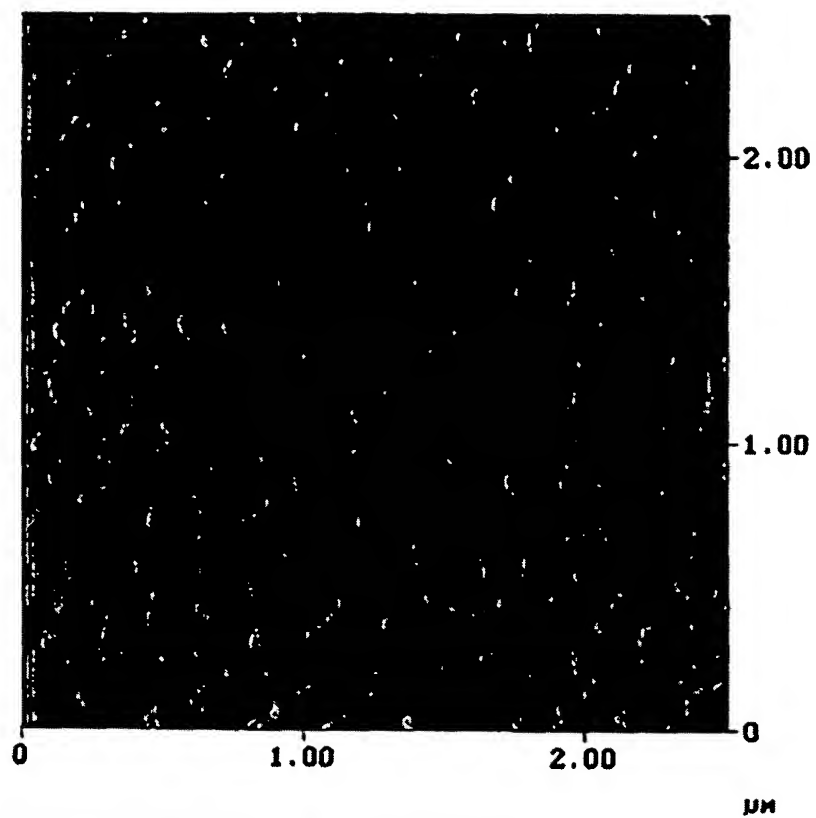


FIG. 15



Rms: 13.39 nm Ra: 2.84 nm μm

FIG. 16



Rms: 6.48 nm Ra: 2.65 nm

FIG. 17

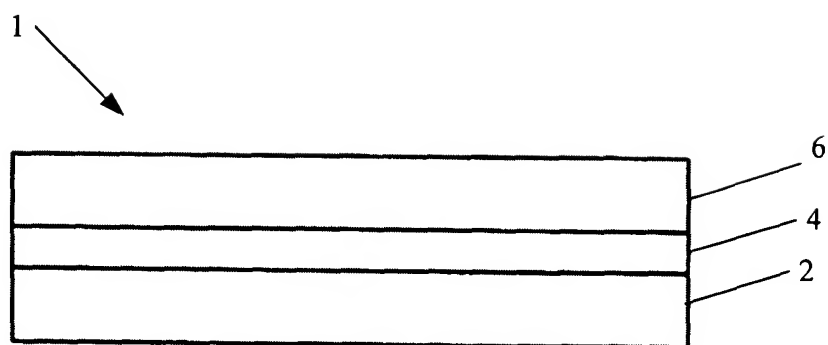


FIG. 18

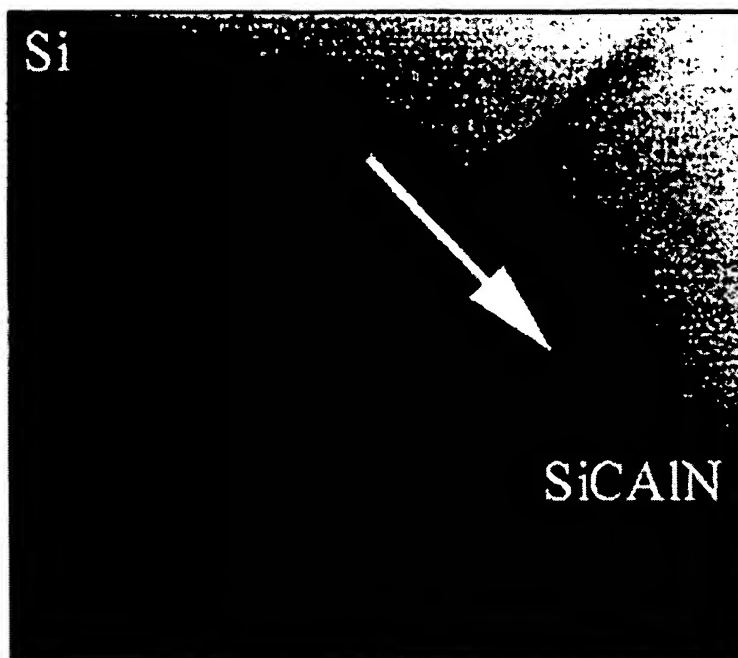


FIG. 19

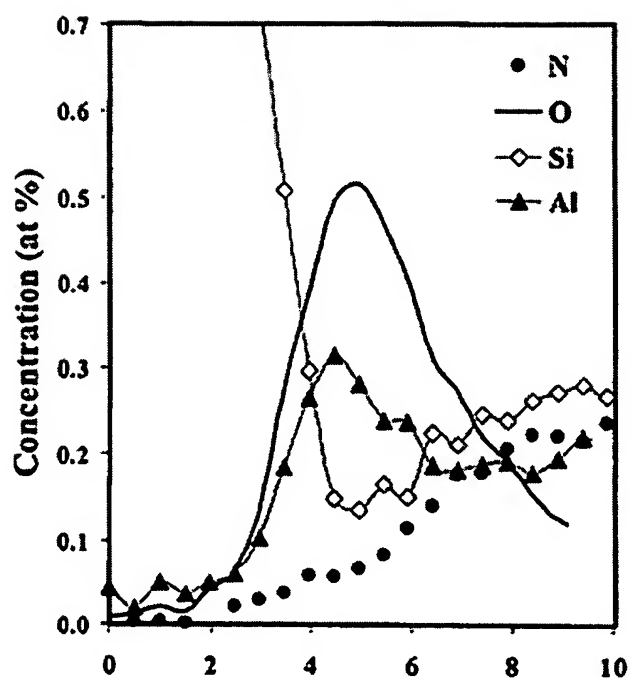


FIG. 20

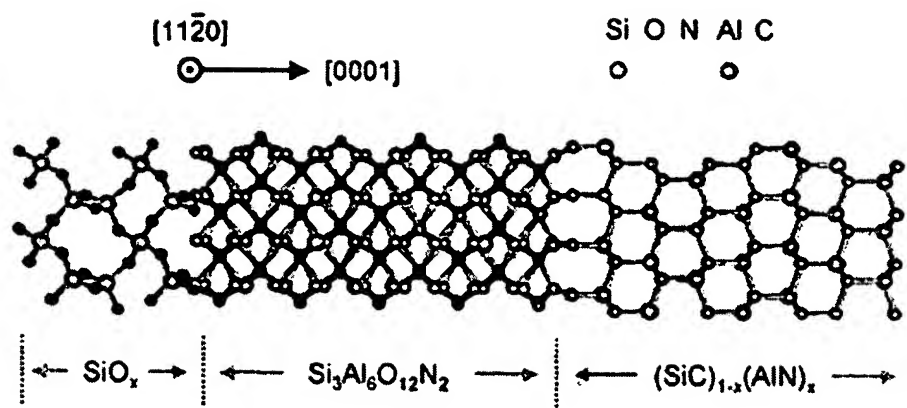


FIG. 21

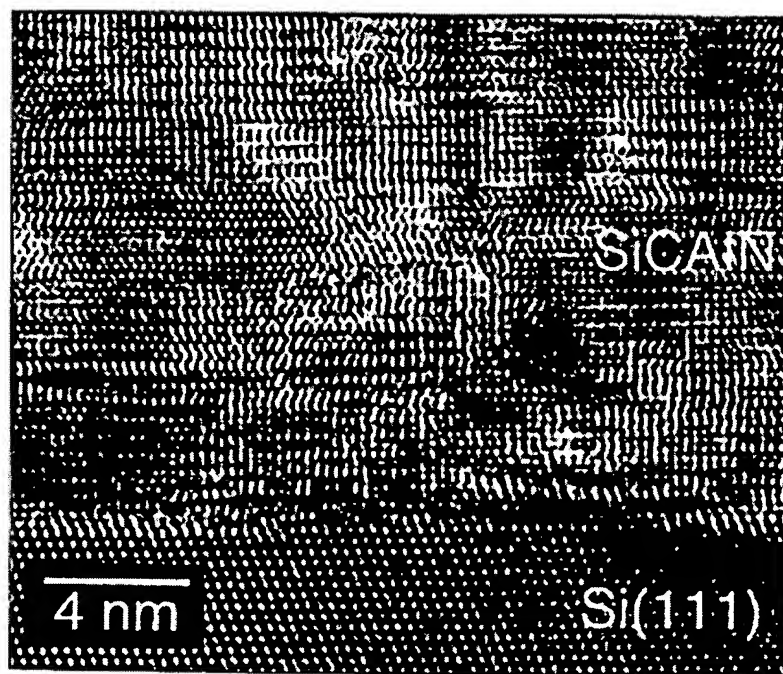


FIG. 22

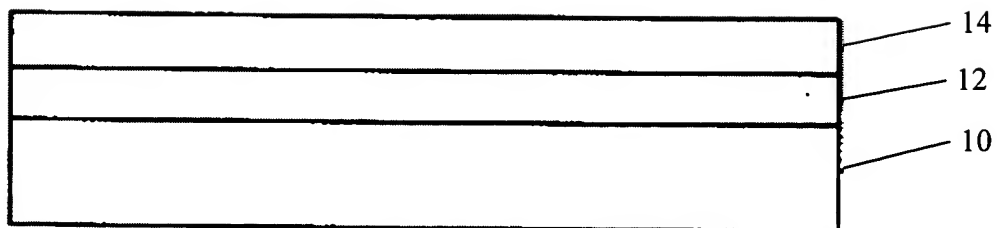
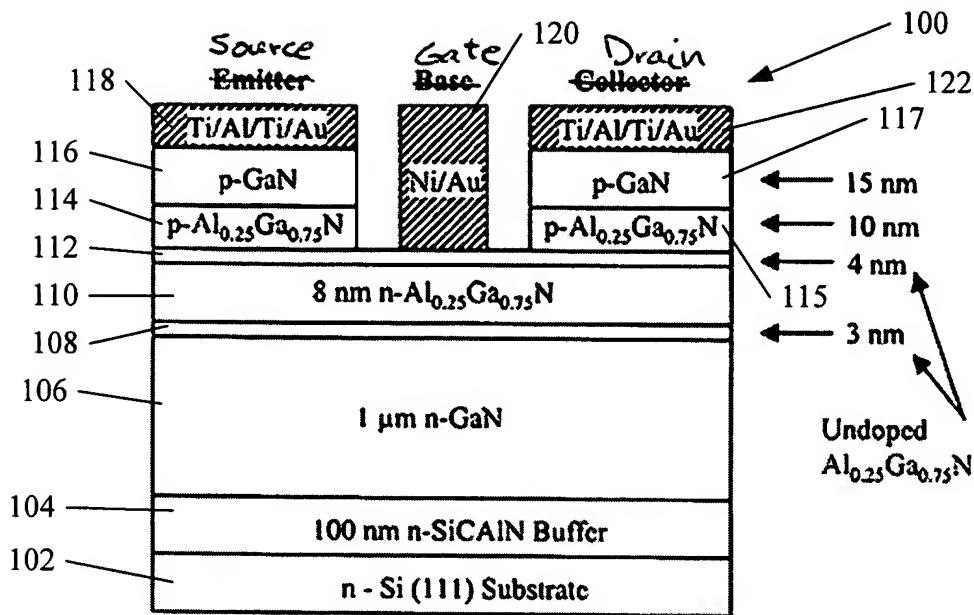
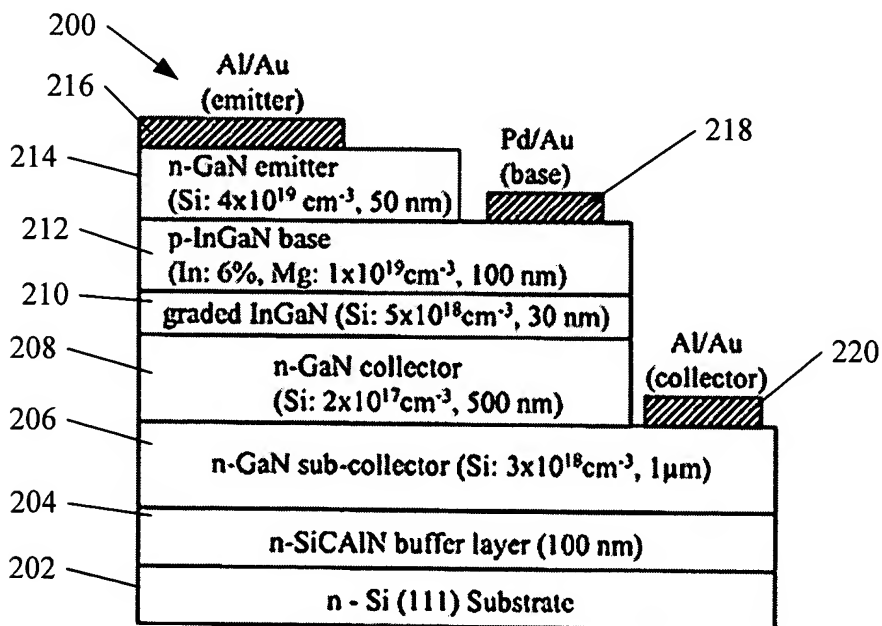


FIG. 23



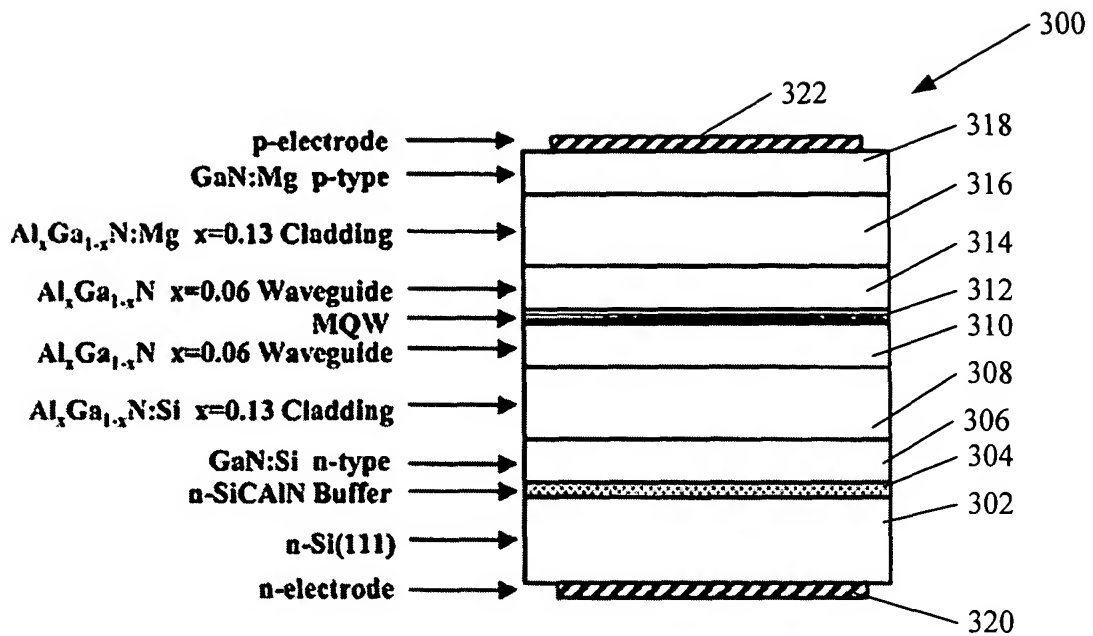
AlGaIn/GaN heterostructure field effect transistor (HFET)

FIG. 24



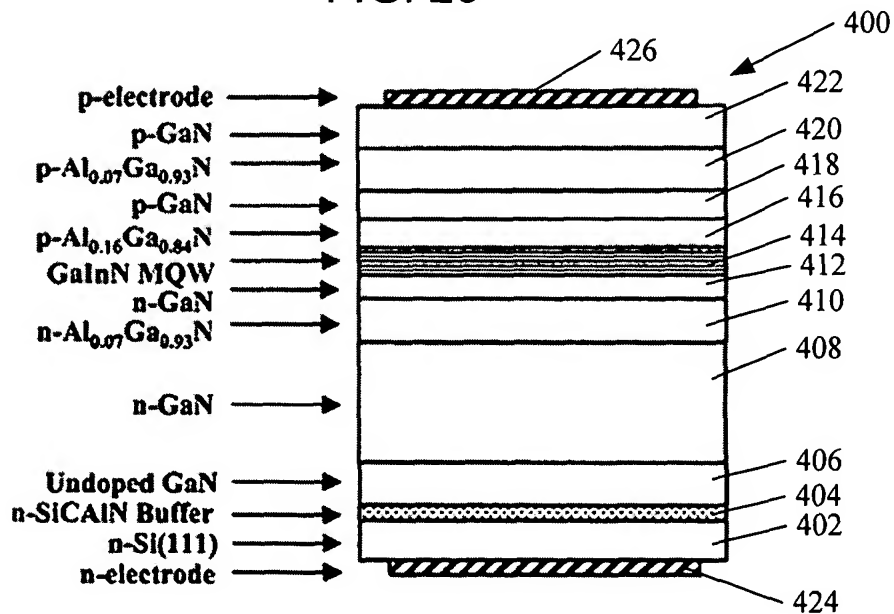
Layer structure of InGaIn/GaN heterojunction bipolar transistor (HBT)

FIG. 25



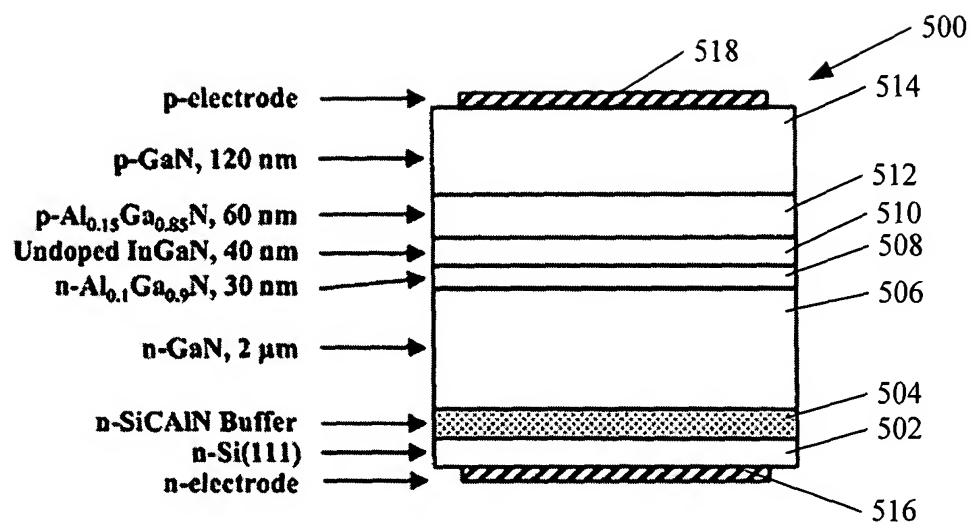
Schematic of a typical laser structure
on SiCAIN/Si(111) substrate

FIG. 26



Schematic cross section of GaInN MQW laser diodes
on SiCAIN/Si(111) substrate

FIG. 27



The structure of the UV LEDs on SiCAlN/Si(111) substrate

FIG. 28